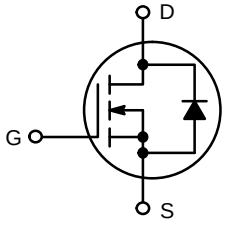
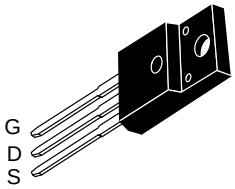
MOSFET – Power, N-Channel, SUPERFET® III, FAST

650 V, 250 mΩ, 13 A

NTPF250N65S3H

V_{DSS}	$R_{DS(ON)}$ MAX	I_D MAX
650 V	250 mΩ @ 10 V	13 A





TO−220 FULLPAK
CASE 221D

Description

SUPERFET III MOSFET is **onsemi**'s brand-new high voltage super-junction (SJ) MOSFET family that is utilizing charge balance technology for outstanding low on-resistance and lower gate charge performance. This advanced technology is tailored to minimize conduction loss, provides superior switching performance, and withstand extreme dv/dt rate.

Consequently, SUPERFET III FAST MOSFET series helps minimize various power systems and improve system efficiency.

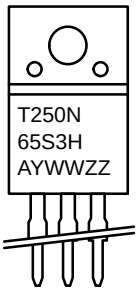
Features

- 700 V @ T_J = 150°C
- Typ. $R_{DS(on)}$ = 201 mΩ
- Ultra Low Gate Charge (Typ. Q_g = 24 nC)
- Low Effective Output Capacitance (Typ. $C_{oss(eff.)}$ = 229 pF)
- 100% Avalanche Tested
- These Devices are Pb−Free and are RoHS Compliant

Applications

- Computing / Display Power Supplies
- Telecom / Server Power Supplies
- Industrial Power Supplies
- Lighting / Charger / Adapter

MARKING DIAGRAM



T250N65S3H	= Specific Device Code
A	= Assembly Location
YWW	= Date Code (Year & Week)
ZZ	= Assembly Lot

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

ABSOLUTE MAXIMUM RATINGS (T_C = 25°C, Unless otherwise specified)

Symbol	Parameter		Value	Unit
V_{DSS}	Drain to Source Voltage		650	V
V_{GSS}	Gate to Source Voltage	DC	±30	V
		AC (f > 1 Hz)	±30	V
I_D	Drain Current	Continuous (T_C = 25°C)	13*	A
		Continuous (T_C = 100°C)	8*	
I_{DM}	Drain Current	Pulsed (Note 1)	36*	A
E_{AS}	Single Pulsed Avalanche Energy (Note 2)		108	mJ
I_{AS}	Avalanche Current (Note 2)		2.9	A
E_{AR}	Repetitive Avalanche Energy (Note 1)		1.06	mJ
dv/dt	MOSFET dv/dt		120	V/ns
	Peak Diode Recovery dv/dt (Note 3)		20	
P_D	Power Dissipation	(T_C = 25°C)	29	W
		Derate Above 25°C	0.23	W/°C
T_J, T_{STG}	Operating and Storage Temperature Range		−55 to +150	°C
T_L	Maximum Lead Temperature for Soldering, 1/8″ from Case for 5 s		260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.
*Drain current limited by maximum junction temperature.
1. Repetitive rating: pulse-width limited by maximum junction temperature.
2. I_{AS} = 2.9 A, R_G = 25 Ω, starting T_J = 25°C.
3. I_{SD} ≤ 6.5 A, di/dt ≤ 200 A/μs, V_{DD} ≤ 400 V, starting T_J = 25°C.

THERMAL CHARACTERISTICS

Symbol	Parameter	Value	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	4.23	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	62.5	

PACKAGE MARKING AND ORDERING INFORMATION

Part Number	Top Marking	Package	Shipping
NTPF250N65S3H	T250N65S3H	TO−220 FULLPAK	1000 Units / Tube

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Symbol	Parameter	Test Conditions	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
BV_{DSS}	Drain to Source Breakdown Voltage	V_{GS} = 0 V, I_D = 1 mA, T_J = 25°C	650			V
		V_{GS} = 0 V, I_D = 1 mA, T_J = 150°C	700			V
$\Delta BV_{DSS}/\Delta T_J$	Breakdown Voltage Temperature Coefficient	I_D = 10 mA, Referenced to 25°C		0.63		V/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 650 V, V_{GS} = 0 V			1	μA
		V_{DS} = 520 V, T_C = 125°C		0.7		
I_{GSS}	Gate to Body Leakage Current	V_{GS} = ±30 V, V_{DS} = 0 V			±100	nA
ON CHARACTERISTICS						
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS} = V_{DS}, I_D = 1.1 mA	2.4		4.0	V
$R_{DS(on)}$	Static Drain to Source On Resistance	V_{GS} = 10 V, I_D = 6.5 A		201	250	mΩ
g_{FS}	Forward Transconductance	V_{DS} = 20 V, I_D = 6.5 A		14		S
DYNAMIC CHARACTERISTICS						
C_{iss}	Input Capacitance	V_{DS} = 400 V, V_{GS} = 0 V, f = 250 kHz		1261		pF
C_{oss}	Output Capacitance			19		pF
$C_{oss(eff.)}$	Effective Output Capacitance	V_{DS} = 0 V to 400 V, V_{GS} = 0 V		229		pF
$C_{oss(er.)}$	Energy Related Output Capacitance	V_{DS} = 0 V to 400 V, V_{GS} = 0 V		33		pF
$Q_{g(tot)}$	Total Gate Charge at 10 V	V_{DS} = 400 V, I_D = 6.5 A, V_{GS} = 10 V (Note 4)		24		nC
Q_{gs}	Gate to Source Gate Charge			5.9		nC
Q_{gd}	Gate to Drain “Miller” Charge			6.8		nC
ESR	Equivalent Series Resistance	f = 1 MHz		0.9		Ω
SWITCHING CHARACTERISTICS						
$t_{d(on)}$	Turn-On Delay Time	V_{DD} = 400 V, I_D = 6.5 A, V_{GS} = 10 V, R_g = 12 Ω (Note 4)		18		ns
t_r	Turn-On Rise Time			8.2		ns
$t_{d(off)}$	Turn-Off Delay Time			54		ns
t_f	Turn-Off Fall Time			4.2		ns
SOURCE-DRAIN DIODE CHARACTERISTICS						
I_S	Maximum Continuous Source to Drain Diode Forward Current				13	A
I_{SM}	Maximum Pulsed Source to Drain Diode Forward Current				36	A
V_{SD}	Source to Drain Diode Forward Voltage	V_{GS} = 0 V, I_{SD} = 6.5 A			1.2	V
t_{rr}	Reverse Recovery Time	V_{DD} = 400 V, I_{SD} = 6.5 A, dI_F/dt = 100 A/μs		233		ns
Q_{rr}	Reverse Recovery Charge			2.5		μC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Essentially independent of operating temperature typical characteristics.

TYPICAL CHARACTERISTICS

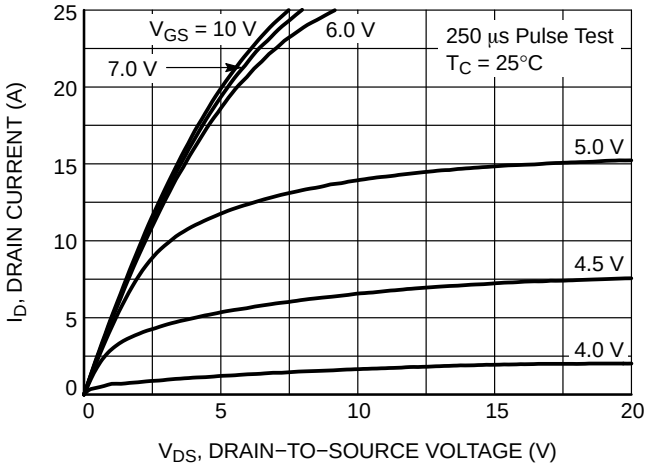


Figure 1. On−Region Characteristics

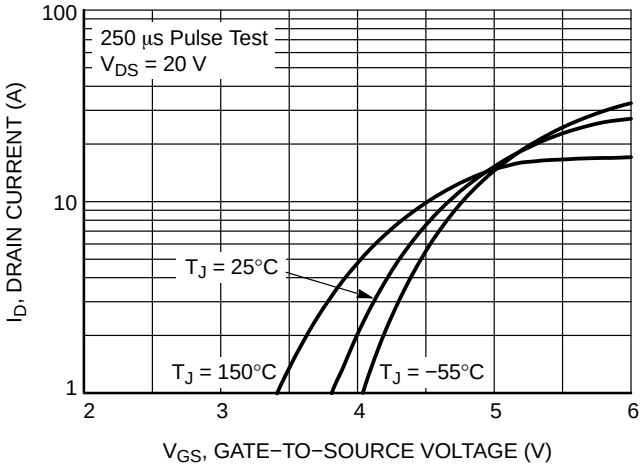


Figure 2. Transfer Characteristics

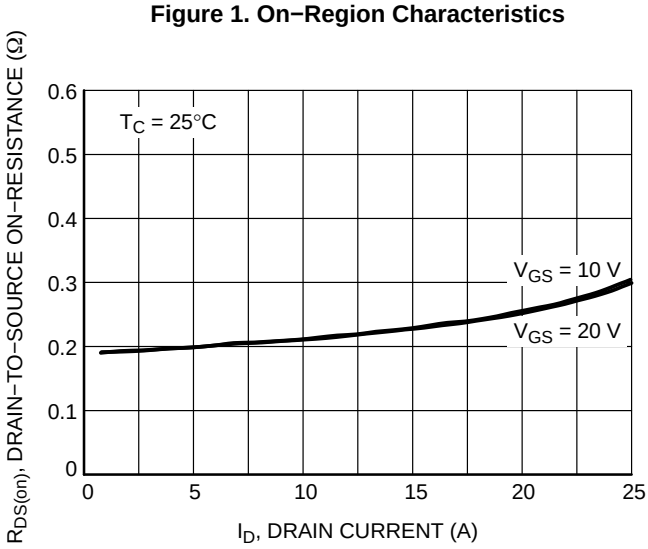


Figure 3. On Resistance Variation vs. Drain Current and Gate Voltage

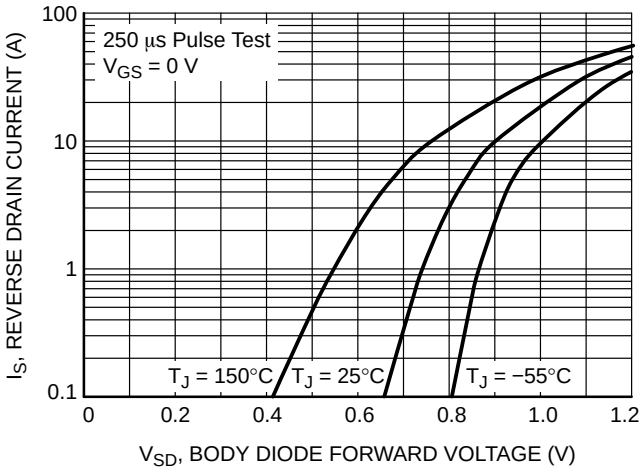


Figure 4. Diode Forward Voltage Variation vs. Source Current and Temperature

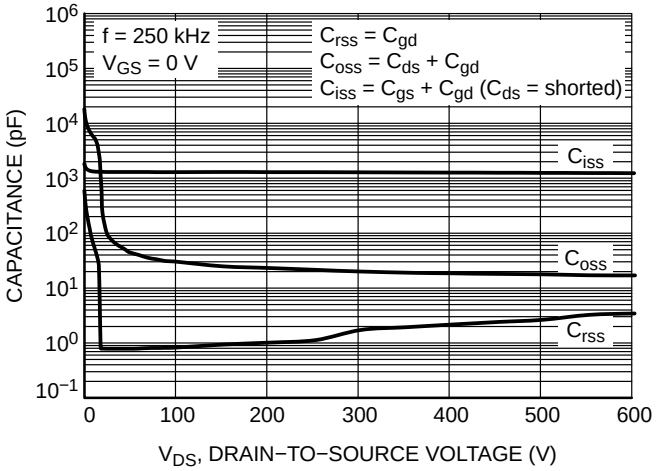


Figure 5. Capacitance Characteristics

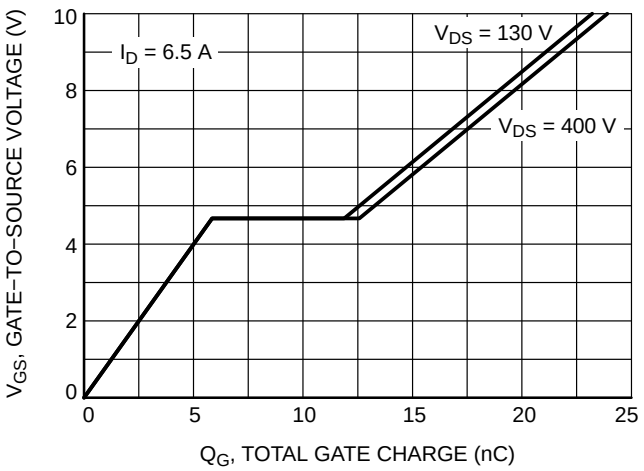


Figure 6. Gate Charge Characteristics

TYPICAL CHARACTERISTICS

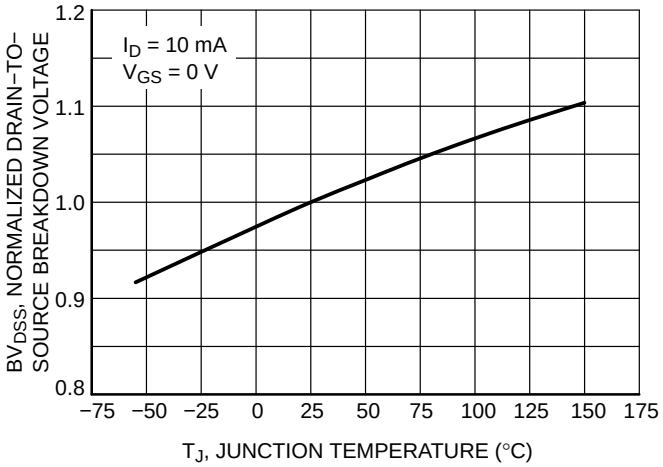


Figure 7. Breakdown Voltage Variation vs. Temperature

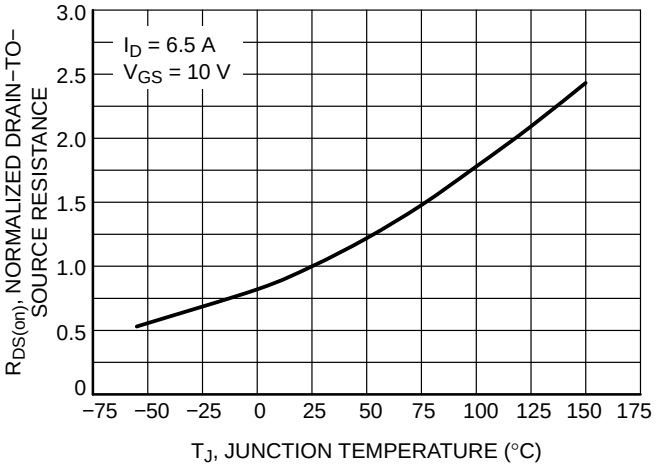


Figure 8. On−Resistance Variation vs. Temperature

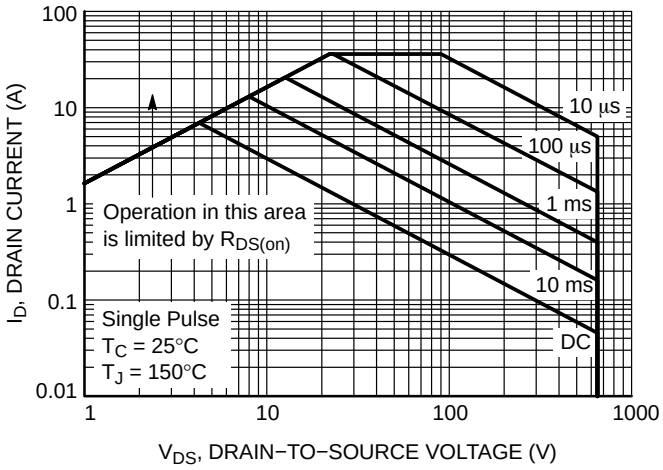


Figure 9. Maximum Safe Operating Area

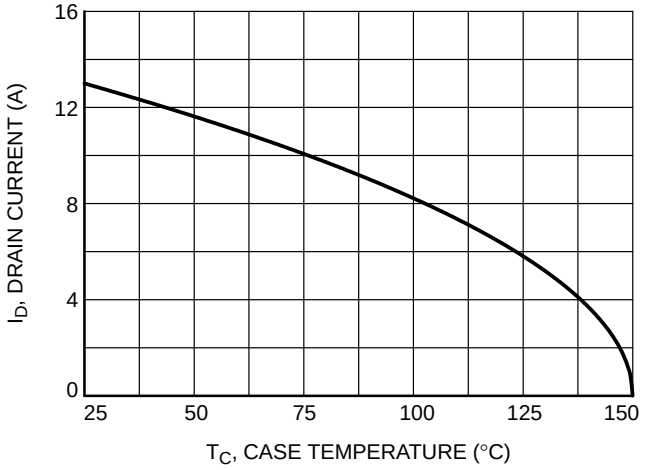


Figure 10. Maximum Drain Current vs. Case Temperature

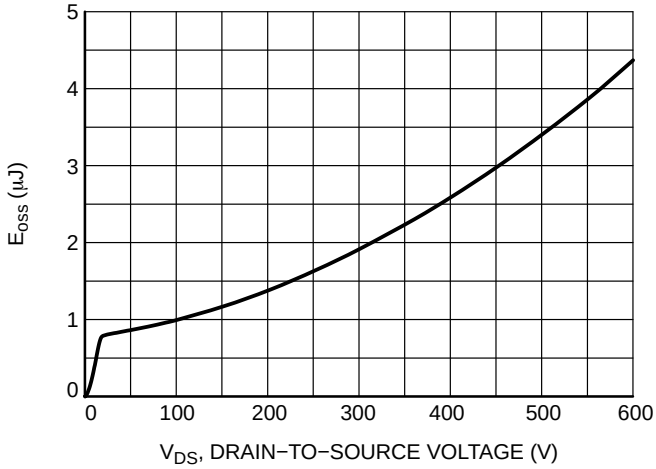


Figure 11. E_{oss} vs. Drain−to−Source Voltage

TYPICAL CHARACTERISTICS

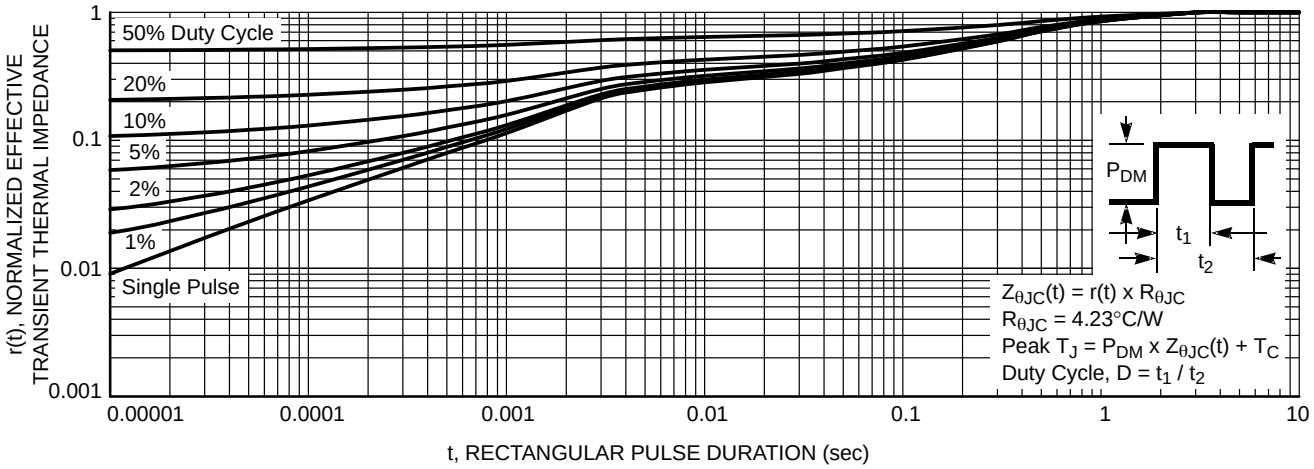


Figure 12. Transient Thermal Response Curve

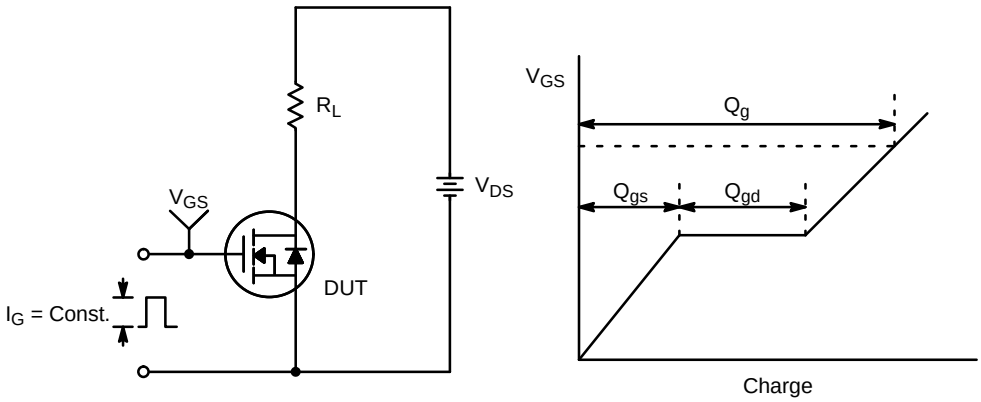


Figure 13. Gate Charge Test Circuit & Waveform

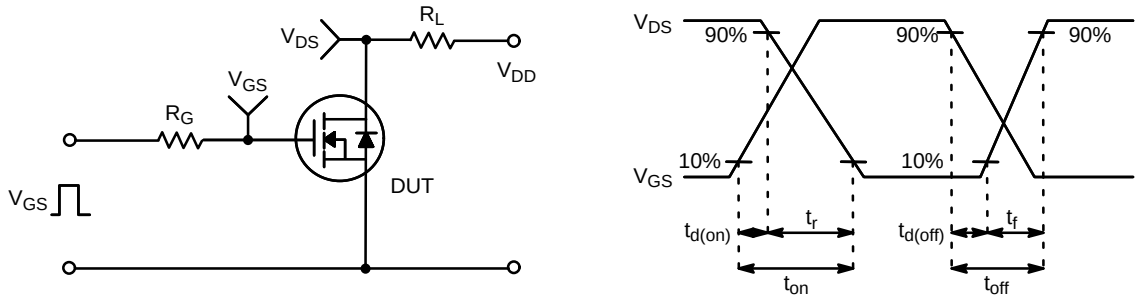


Figure 14. Resistive Switching Test Circuit & Waveforms

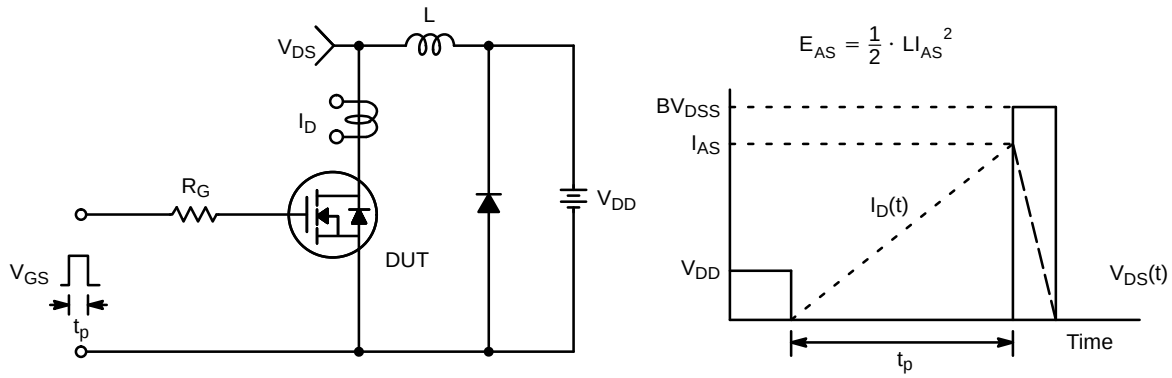


Figure 15. Unclamped Inductive Switching Test Circuit & Waveforms

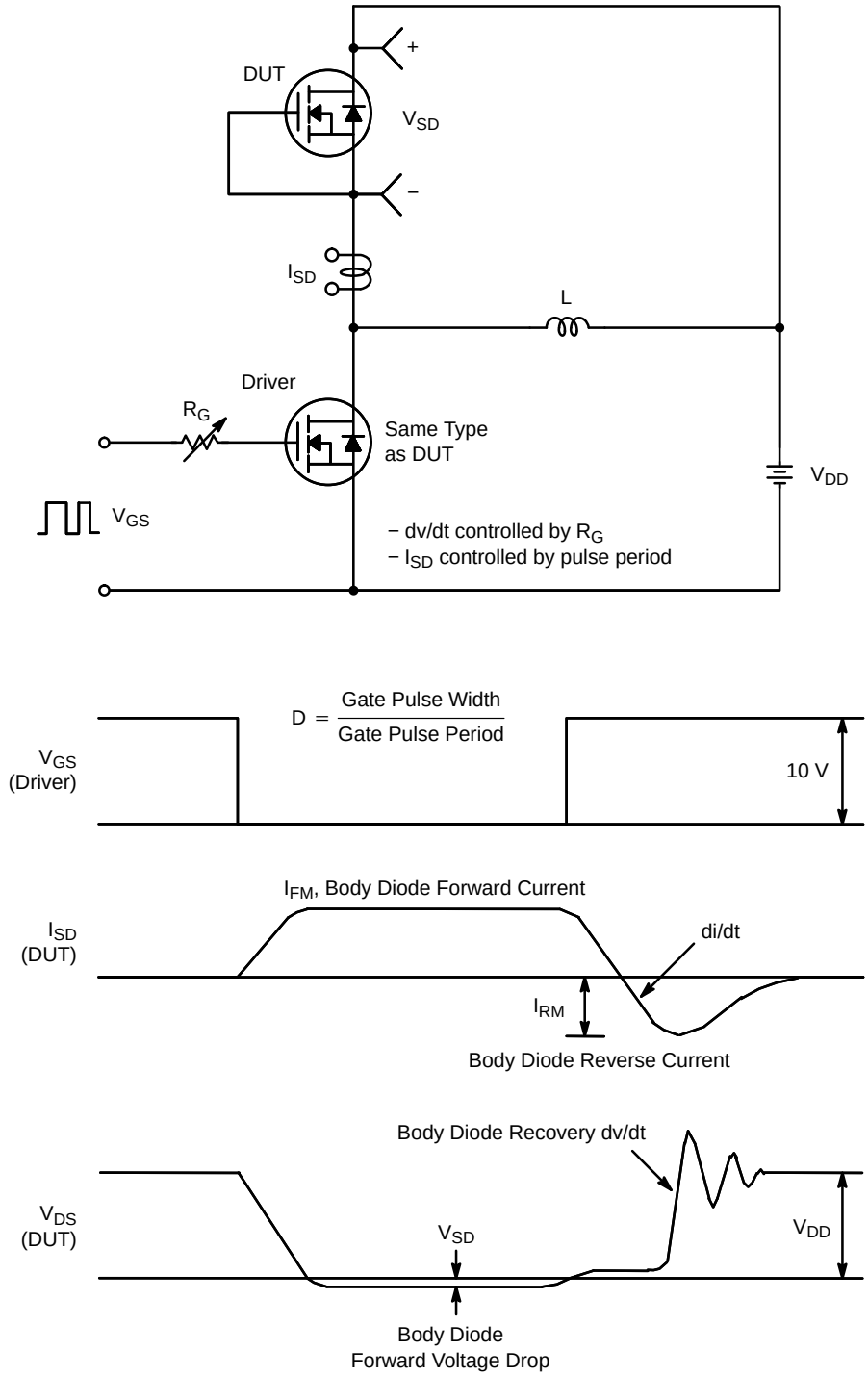
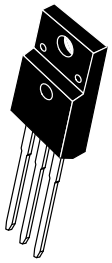


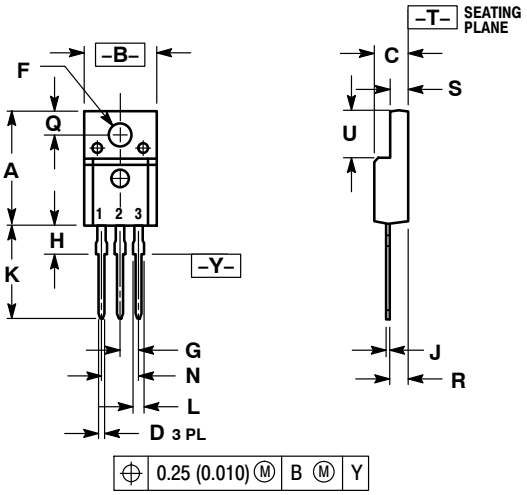
Figure 16. Peak Diode Recovery dv/dt Test Circuit & Waveforms



SCALE 1:1

TO−220 FULLPAK
CASE 221D−03
ISSUE K

DATE 27 FEB 2009



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH
3. 221D−01 THRU 221D−02 OBSOLETE, NEW STANDARD 221D−03.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.617	0.635	15.67	16.12
B	0.392	0.419	9.96	10.63
C	0.177	0.193	4.50	4.90
D	0.024	0.039	0.60	1.00
F	0.116	0.129	2.95	3.28
G	0.100 BSC		2.54 BSC	
H	0.118	0.135	3.00	3.43
J	0.018	0.025	0.45	0.63
K	0.503	0.541	12.78	13.73
L	0.048	0.058	1.23	1.47
N	0.200 BSC		5.08 BSC	
Q	0.122	0.138	3.10	3.50
R	0.099	0.117	2.51	2.96
S	0.092	0.113	2.34	2.87
U	0.239	0.271	6.06	6.88

STYLE 1:
PIN 1. GATE
2. DRAIN
3. SOURCE

STYLE 2:
PIN 1. BASE
2. COLLECTOR
3. EMITTER

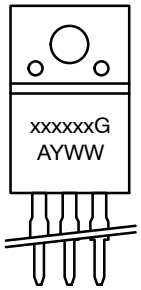
STYLE 3:
PIN 1. ANODE
2. CATHODE
3. ANODE

STYLE 4:
PIN 1. CATHODE
2. ANODE
3. CATHODE

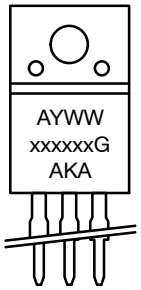
STYLE 5:
PIN 1. CATHODE
2. ANODE
3. GATE

STYLE 6:
PIN 1. MT 1
2. MT 2
3. GATE

MARKING DIAGRAMS



Bipolar



Rectifier

xxxxxx	= Specific Device Code
G	= Pb−Free Package
A	= Assembly Location
Y	= Year
WW	= Work Week

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Y	= Year
WW	= Work Week
xxxxxx	= Device Code
G	= Pb−Free Package
AKA	= Polarity Designator

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